

Curs 8
Electronica Digitala
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BUCURESTI
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CALCULATOARE

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1 Circuit logic N-MOS

Avem tensiune de 0 volti \Rightarrow tranzistorul este blocat \Rightarrow tensiunea de iesire este $V_{CC} \Rightarrow$ graficul va fi constant.

Daca mai crestem V_T -ul, o sa intre in conductie in continuare dar tensiunea de intrare este mai mica decat V_T iar tensiunea de iesire este mai mare decat $V_{GS} - V_T \Rightarrow$ saturatie.

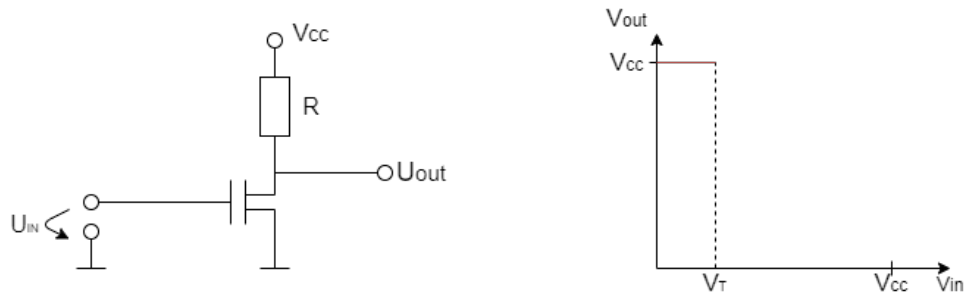


Figure 1: Inversor cu tranzistorul in regiunea de saturatie

Tensiunea de iesire scade \Rightarrow

$$V_{DS} = V_{out}$$

$$V_{GS} = V_{in}$$

V_{DS} se intersecteaza cu $V_{GS} - V_T \Rightarrow$ exista un punct unde tranzistorul trece din regiunea de saturatie in regiunea liniara.

O poarta va avea tensiunea de iesire corecta pentru orice tensiune mai mica decat V_T la intrare. V_{IH} tensiunea minima de intrare pentru care poarta interpreteaza 1 logic.

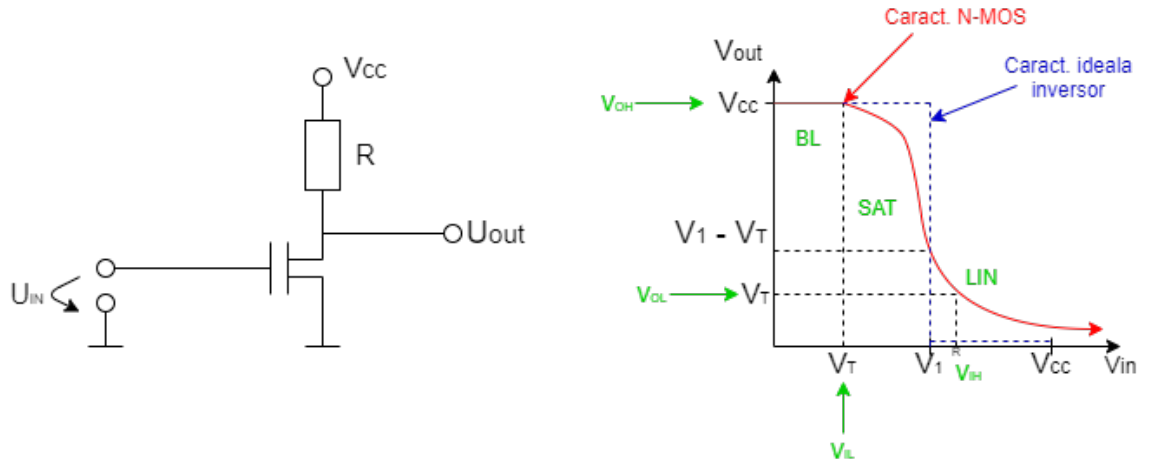


Figure 2: Inversor cu tranzistorul in regiunea liniara

$$V_1 = \begin{cases} V_{CC} = I_D * R + V_{DS} \\ I_D = \frac{K}{2} * (V_{GS} - V_T)^2 \\ V_{GS} - V_T = V_{DS} \end{cases} \quad \begin{cases} V_T = 2V \\ V_{CC} = 5V \\ K = 6mA/V^2 \\ R = 2K \end{cases}$$

$$I_D = \frac{K}{2} * V_{DS}^2$$

$$\frac{R*K}{2} * V_{DS}^2 + V_{DS} = V_{GC}$$

$$4V_{DS}^2 + V_{DS} = 5V \Rightarrow$$

$$V_1 = \begin{cases} V_{DS} = 1V \\ V_{GS} = 3V \end{cases}$$

$$\begin{array}{ll} V_{GS} < V_T = 2V & T = BL \\ 2V < V_{GS} < 3V & T = SAT \\ 3 < V_{GS} & T = LIM \end{array}$$

$$\begin{aligned} V_{IN} = 5V : I_D &= \frac{K}{2} (V_{GS} - V_T) V_{DS} = \\ &= \frac{8mA/V^2}{2} (5V - 2V) * V_{DS} = \\ &= 12mA/V * V_{DS} \end{aligned}$$

$$\begin{aligned} V_{CC} &= RI_D + V_{DS} \\ 5 &= 2K * 12mA/V * V_{DS} + V_{DS} \end{aligned}$$

$$\Rightarrow V_{DS} = \frac{5}{13} = 0.38V$$

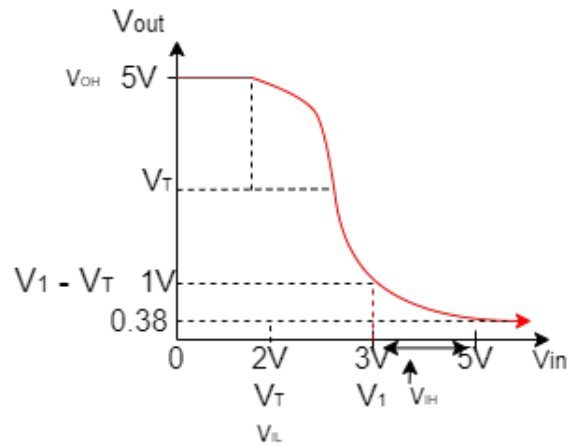


Figure 3

Alegem $V_{IH} = 3V$, $V_{IL} = 2V$, $V_{OH} = 5V$, $V_{OL} = 1V$

$$\Rightarrow MZL = 1V = V_{IL} - V_{OL}, MZH = 2V = V_{OH} - V_{IH}$$

2 Analiza tensiunii de iesire pentru o poarta N-MOS

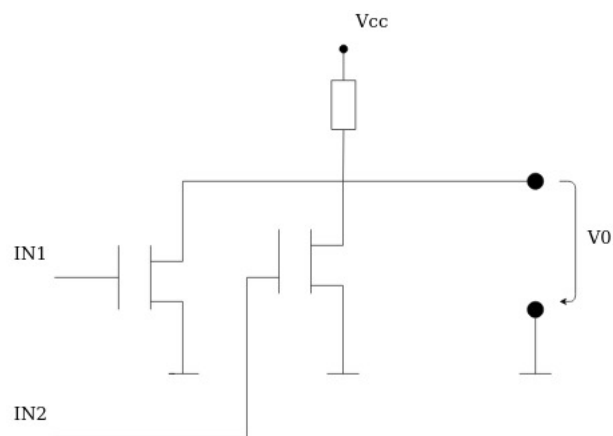


Figure 4: Poarta NOR

IN_1	IN_2	U_0
$0V$	$0V$	V_{CC}
V_{CC}	$0V$	V_{OL}
$0V$	V_{CC}	V_{OL}
V_{CC}	V_{CC}	$< V_{OL}$

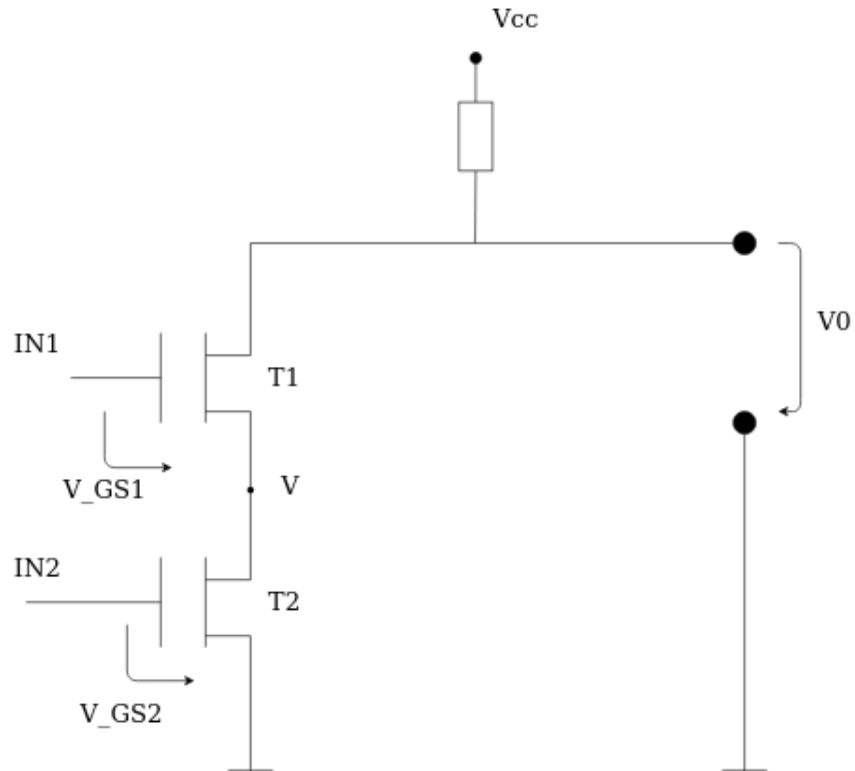


Figure 5: Poarta NAND

$$V_{GS2} = U_2$$

$$V_{GS1} = U_1 - V \text{ (unde } V \text{ este potentialul)}$$

În continuare o să luăm o poartă de tip N-MOS și vom analiza cum arată tensiunea de ieșire pentru un impuls ideal la intrare.

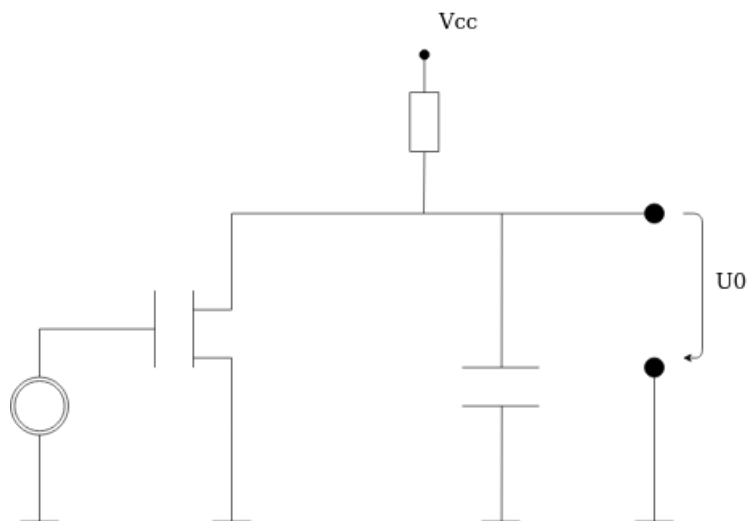


Figure 6

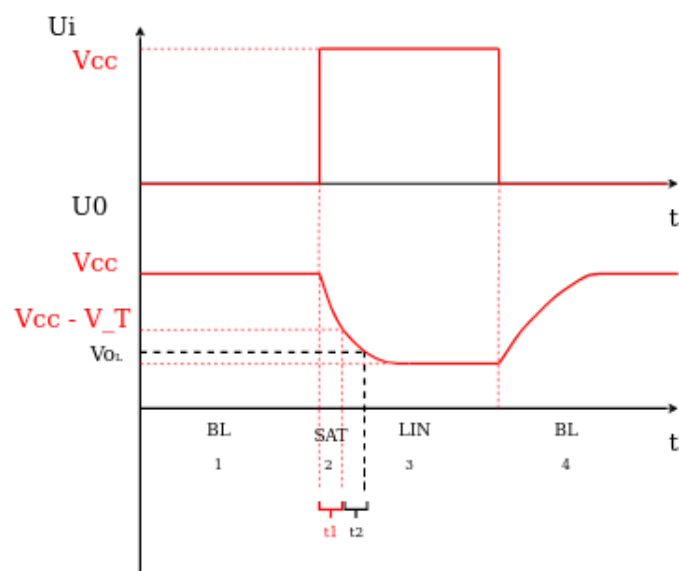


Figure 7

Pentru regiunea 1 tranzistorul este BLOCAT (BL) si schema echivalenta va

fi urmatoarea:

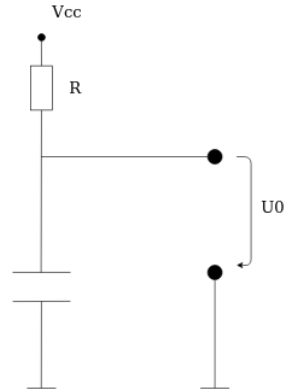


Figure 8

$$U_0 = V_{CC}$$

Pentru regiunea 2:

$$\text{INITIAL: } V_{IN} = V_{GS} = V_{CC}, U_0 = U_C = V_{CC} = V_{DS}$$

$$V_{DS} > V_{CS} - V_T$$

\Rightarrow Tranzistorul este in regiunea SATURATA (SAT)

$$V_{CCC} > V_{CC} - V_T$$

Se comporta ca o sursa de curent:

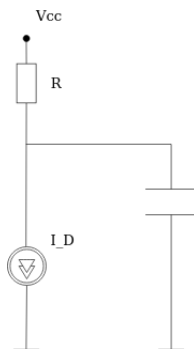


Figure 9

$$I_D = \frac{K}{2} * (V_{GS} - V_T)^2 = \frac{K}{2} * (V_{CC} - V_T)^2$$

Facem o echivalenta Thevenin a acestei rezistente cu condensator. Aceasta va deveni o sursa de tensiune si o rezistenta.

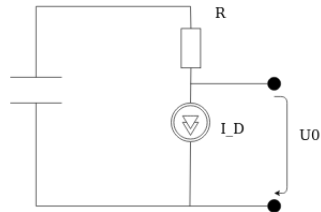


Figure 10

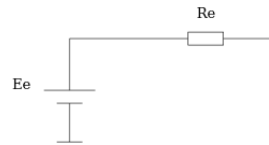


Figure 11

$$E_e = V_{CC} - RI_D$$

$$R_e = R$$

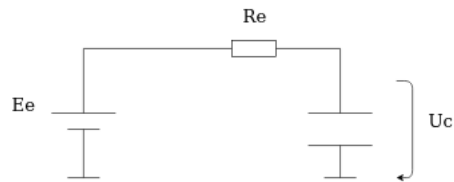


Figure 12

$$U_C(0) = V_{CC}$$

$$U_C(\infty) = E_e \quad \Rightarrow \quad U_C(t) = V_{CC} * e^{-t/\tau} + E_e * (1 - e^{-t/\tau})$$

$$\tau = RC$$

Aceasta este formula graficului in regiunea SAT.

Numim prima parte a comutarii (pana cand tensiunea de iesire U_0 ajunge la $V_{CC} - V_T$) t_1 .

$$U_C(t_1) = V_{CC} - V_T = V_{CC} * e^{-t_1/\tau} + E_e * (1 - e^{-t_1/\tau})$$

Pentru partea a doua a comutarii tranzistorul este in regiunea 3: LINIARA (LIN)

$$V_{DS} < V_{CC} - V_T$$

$$V_{GS} < V_{CC}$$

\Rightarrow Tranzistorul este in regiunea LINIARA si se comporta ca o rezistenta
 $R_{eT} = \frac{1}{\frac{k}{2}(V_{GS} - V_T)}$

Schema echivalenta:

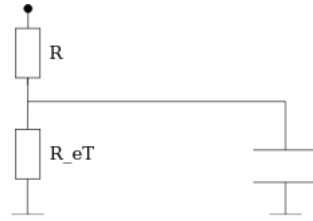


Figure 13

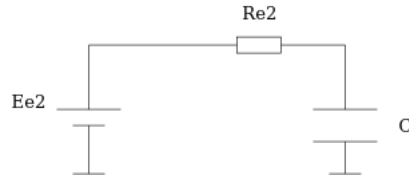


Figure 14

$$E_{e2} = V_{CC} \frac{R_{eT}}{R + R_{eT}}$$

$$R_{e2} = R \parallel R_{eT}$$

$$U_C(0) = V_{CC} - V_T$$

$$U_C(\infty) = E_{e2} = V_{CC} \frac{R_{eT}}{R + R_{eT}}$$

$$\tau_2 = R_{e2}C$$

Astfel ecuatia curbei noastre va fi:

$$U_C(t) = (V_{CC} - V_T)e^{-t/\tau_2} + V_{CC} \frac{R_{eT}}{R + R_{eT}} (1 - e^{-t/\tau_2})$$

Ne intereseaza momentul in care tensiunea de iesire coboara sub V_{OL} , adica t_2 .

$$U_C(t_2) = V_{OL}$$